

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises an SOI substrate, a trench, a trench capacitor, and a conductive layer. The SOI substrate includes a first semiconductor region, a buried insulating film formed on the first semiconductor region, and a second semiconductor region formed on the buried insulating film. The trench is of a depth to reach the first semiconductor region, extending from a surface of the second semiconductor region on the SOI substrate and passing through the buried insulating film. The trench capacitor is formed within the trench. The conductive layer is formed in a region between a sidewall portion of the trench and the buried insulating film, and electrically connects the first semiconductor region and the second semiconductor region.